Vishay Semiconductors

Hyperfast Rectifier, 4 A FRED Pt[®]



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DPAK (TO-252AA)

PRIMARY CHARACTERISTICS				
I _{F(AV)}	4 A			
V _R	200 V			
V _F at I _F	0.71 V			
t _{rr} (typ.)	23 ns			
T _J max.	175 °C			
Package	DPAK (TO-252AA)			
Circuit configuration	Single			

FEATURES

- Hyperfast recovery time
- 175 °C max. operating junction temperature
- Output rectification freewheeling
- Low forward voltage drop reduced Q_{rr} and soft recovery
- Low leakage current
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V _{RRM}		200	V	
Average rectified forward current	I _{F(AV)}	T _C = 164 °C	4		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	А	
Peak repetitive forward current	I _{FM}	$T_{C} = 164 \ ^{\circ}C, f = 20 \ kHz, d = 50 \ \%$	8		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	N
Converd valtage	M	I _F = 4 A	-	0.87	0.95	V
Forward voltage	V _F	I _F = 4 A, T _J = 150 °C	-	0.71	0.80	
		$V_{R} = V_{R}$ rated	-	-	3	
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	2	20	μA
Junction capacitance	CT	V _R = 200 V	-	17	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH

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RoHS COMPLIANT HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/µs, V _R = 30 V	-	23	-	
Boueres recovery time	+	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	24	-	ns
Reverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	
		T _J = 125 °C		-	27	-	
Deels receiver a current	I _{RRM}	T _J = 25 °C	$I_F = 4 A$	-	2	-	۸
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	3.4	-	A
	T _J = 25 °C	VR = 100 V	-	20	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	46	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	2.7	3.2	°C/W
Approximate weight				0.3		g
Approximate weight				0.01		oz.
Marking device		Case style DPAK (TO-252AA)		4EWH	02FNH	

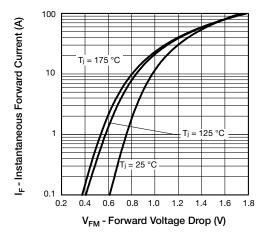


Fig. 1 - Typical Forward Voltage Drop Characteristics

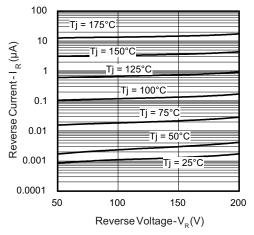


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

VS-4EWH02FNHM3

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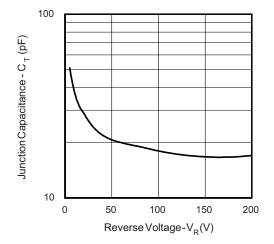
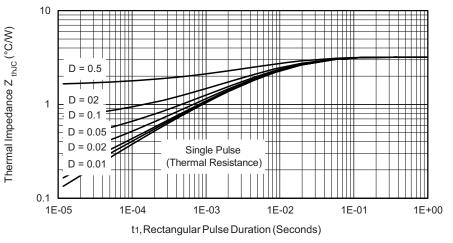
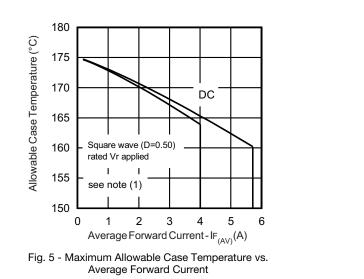
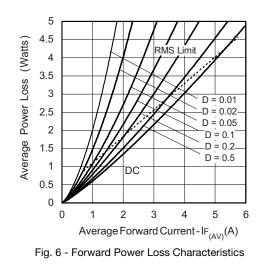


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage









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VS-4EWH02FNHM3

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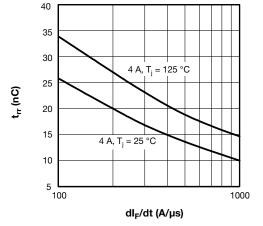


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

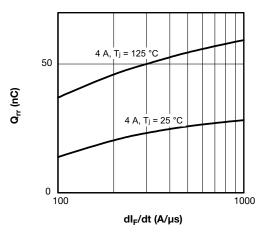


Fig. 8 - Typical Stored Charge vs. dl_F/dt

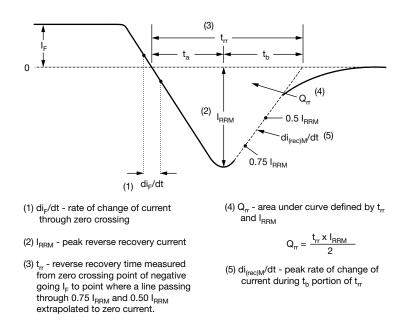


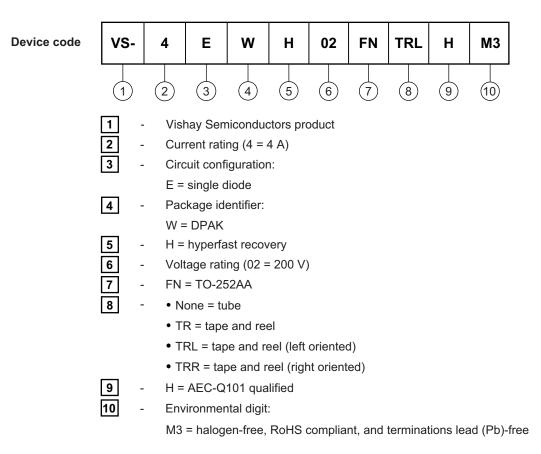
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-4EWH02FNHM3	75	Antistatic plastic tube				
VS-4EWH02FNTRHM3	2000	13" diameter reel				
VS-4EWH02FNTRLHM3	3000	13" diameter reel				
VS-4EWH02FNTRRHM3	3000	13" diameter reel				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95519			
Part marking information	www.vishay.com/doc?95518			
Packaging information	www.vishay.com/doc?95033			
SPICE model	www.vishay.com/doc?95381			

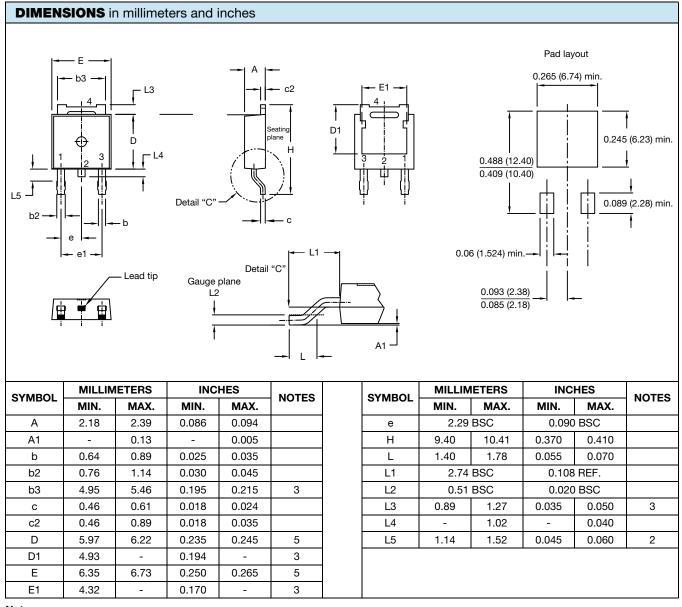
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Outline Dimensions



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Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Dimensions D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁵⁾ Outline conforms to JEDEC[®] outline TO-252AA, except for D1 dimension



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